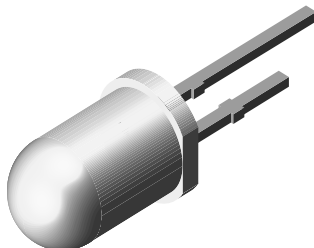


# Infrared Emitting Diode, 950 nm, GaAs



94 8390

## FEATURES

- Package type: leaded
- Package form: T-1¾
- Dimensions (in mm): Ø 5
- Peak wavelength:  $\lambda_p = 950$  nm
- High reliability
- Angle of half intensity:  $\phi = \pm 15^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
**GREEN**  
(5-2008)

## DESCRIPTION

TSUS6202 is an infrared, 950 nm emitting diode in GaAs technology molded in a blue-gray tinted plastic package.

## APPLICATIONS

- Emitter in transmissive sensors
- Emitter in reflective sensors

## PRODUCT SUMMARY

| COMPONENT | $I_e$ (mW/sr) | $\phi$ (deg) | $\lambda_p$ (nm) | $t_r$ (ns) |
|-----------|---------------|--------------|------------------|------------|
| TSUS6202  | 30            | $\pm 15$     | 950              | 800        |

### Note

- Test conditions see table "Basic Characteristics"

## ORDERING INFORMATION

| ORDERING CODE | PACKAGING | REMARKS                      | PACKAGE FORM |
|---------------|-----------|------------------------------|--------------|
| TSUS6202      | Bulk      | MOQ: 4000 pcs, 4000 pcs/bulk | T-1¾         |

### Note

- MOQ: minimum order quantity

## ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25^\circ\text{C}$ , unless otherwise specified)

| PARAMETER                           | TEST CONDITION                         | SYMBOL     | VALUE       | UNIT             |
|-------------------------------------|--|------------|-------------|------------------|
| Reverse voltage                     |  | $V_R$      | 5           | V                |
| Forward current                     |  | $I_F$      | 150         | mA               |
| Peak forward current                | $t_p/T = 0.5, t_p = 100 \mu\text{s}$   | $I_{FM}$   | 300         | mA               |
| Surge forward current               | $t_p = 100 \mu\text{s}$                | $I_{FSM}$  | 2.5         | A                |
| Power dissipation                   |  | $P_V$      | 170         | mW               |
| Junction temperature                |  | $T_j$      | 100         | $^\circ\text{C}$ |
| Operating temperature range         |  | $T_{amb}$  | -40 to +85  | $^\circ\text{C}$ |
| Storage temperature range           |  | $T_{stg}$  | -40 to +100 | $^\circ\text{C}$ |
| Soldering temperature               | $t \leq 5$ s, 2 mm from case           | $T_{sd}$   | 260         | $^\circ\text{C}$ |
| Thermal resistance junction/ambient | J-STD-051, leads 7 mm, soldered on PCB | $R_{thJA}$ | 230         | K/W              |

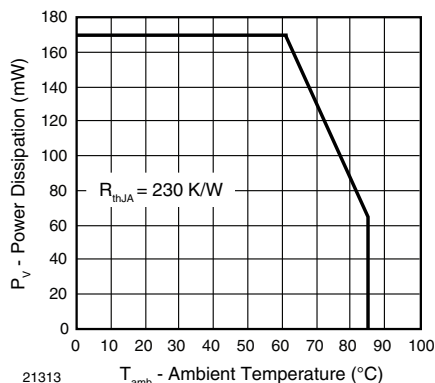


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

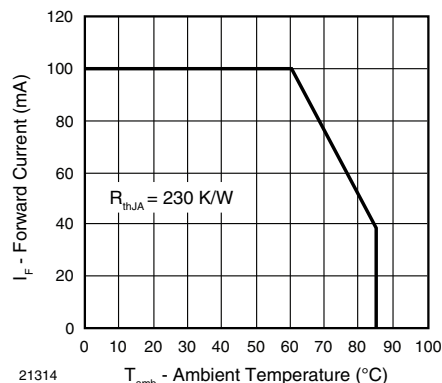


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS ( $T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified) |   |                  |      |          |      |               |
|--|---|------------------|------|----------|------|---------------|
| PARAMETER  | TEST CONDITION  | SYMBOL           | MIN. | TYP.     | MAX. | UNIT          |
| Forward voltage  | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$          | $V_F$            | -    | 1.3      | 1.7  | V             |
|  | $I_F = 1.5\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$ | $V_F$            | -    | 2.2      | 2.7  | V             |
| Temperature coefficient of $V_F$   | $I_F = 100\text{ mA}$                                 | $TK_{V_F}$       | -    | -1.3     | -    | mV/K          |
| Reverse current  | $V_R = 5\text{ V}$                                    | $I_R$            | -    | -        | 100  | $\mu\text{A}$ |
| Junction capacitance   | $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$     | $C_j$            | -    | 30       | -    | pF            |
| Radiant intensity  | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$          | $I_e$            | 20   | 30       | 70   | mW/sr         |
|  | $I_F = 1.5\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$ | $I_e$            | 170  | 280      | -    | mW/sr         |
| Radiant power  | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$          | $\phi_e$         | -    | 15       | -    | mW            |
| Temperature coefficient of $\phi_e$  | $I_F = 20\text{ mA}$                                  | $TK_{\phi_e}$    | -    | -0.8     | -    | %/K           |
| Angle of half intensity  |   | $\phi$           | -    | $\pm 15$ | -    | deg           |
| Peak wavelength  | $I_F = 100\text{ mA}$                                 | $\lambda_p$      | -    | 950      | -    | nm            |
| Spectral bandwidth   | $I_F = 100\text{ mA}$                                 | $\Delta\lambda$  | -    | 50       | -    | nm            |
| Temperature coefficient of $\lambda_p$   | $I_F = 100\text{ mA}$                                 | $TK_{\lambda_p}$ | -    | 0.2      | -    | nm/K          |
| Rise time  | $I_F = 100\text{ mA}$                                 | $t_r$            | -    | 800      | -    | ns            |
|  | $I_F = 1.5\text{ A}$                                  | $t_r$            | -    | 400      | -    | ns            |
| Fall time  | $I_F = 100\text{ mA}$                                 | $t_f$            | -    | 800      | -    | ns            |
|  | $I_F = 1.5\text{ A}$                                  | $t_f$            | -    | 400      | -    | ns            |
| Virtual source diameter  |   | $d$              | -    | 3.8      | -    | mm            |

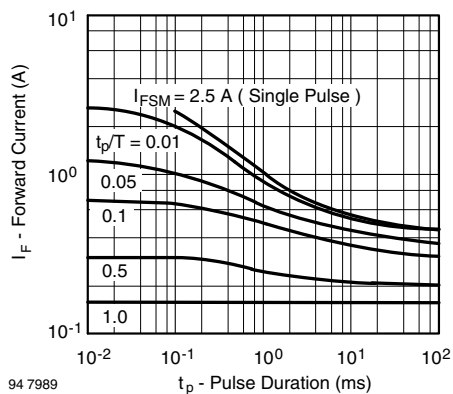
**BASIC CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)


Fig. 3 - Pulse Forward Current vs. Pulse Duration

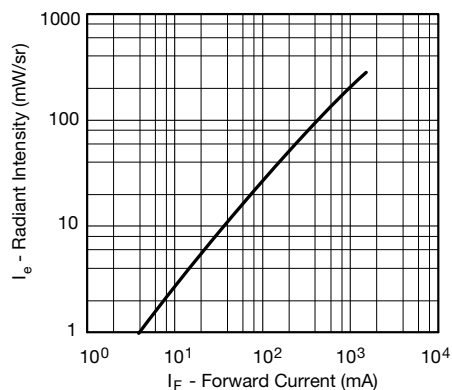


Fig. 6 - Radiant Intensity vs. Forward Current

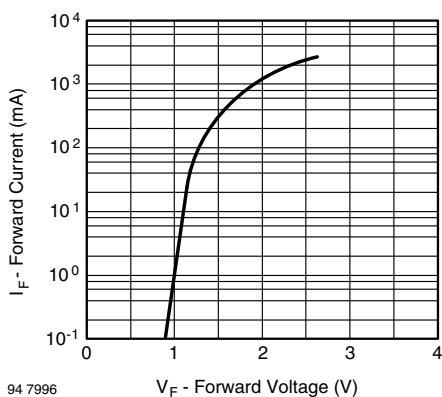


Fig. 4 - Forward Current vs. Forward Voltage

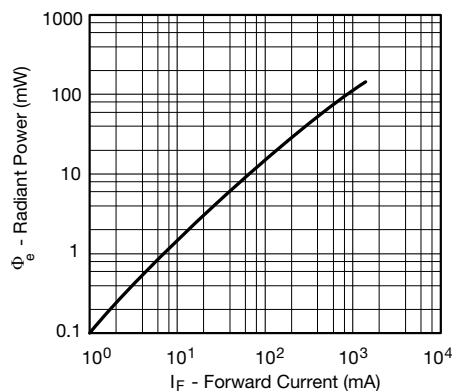


Fig. 7 - Radiant Power vs. Forward Current

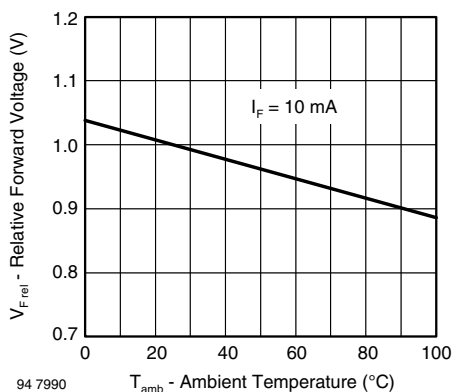


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

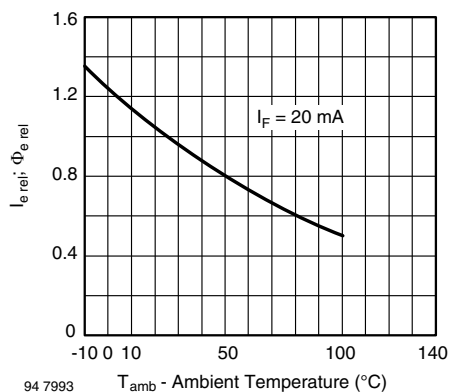


Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature

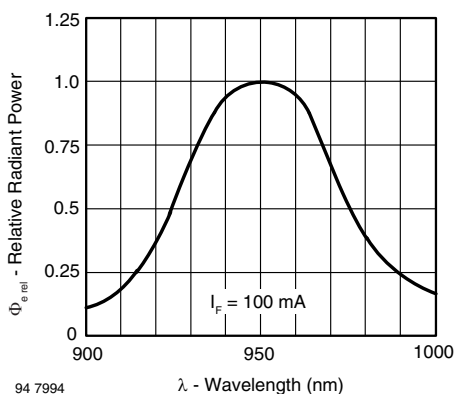


Fig. 9 - Relative Radiant Power vs. Wavelength

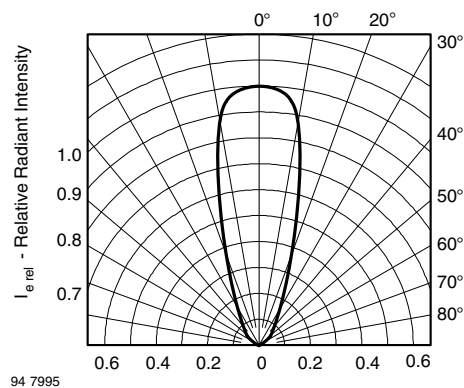
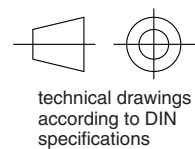
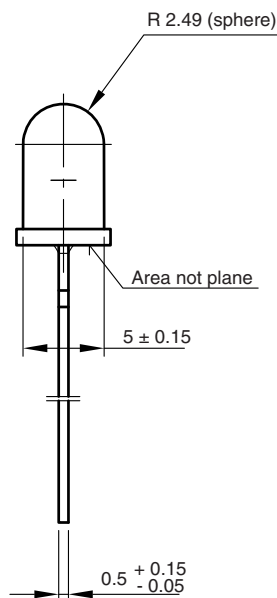
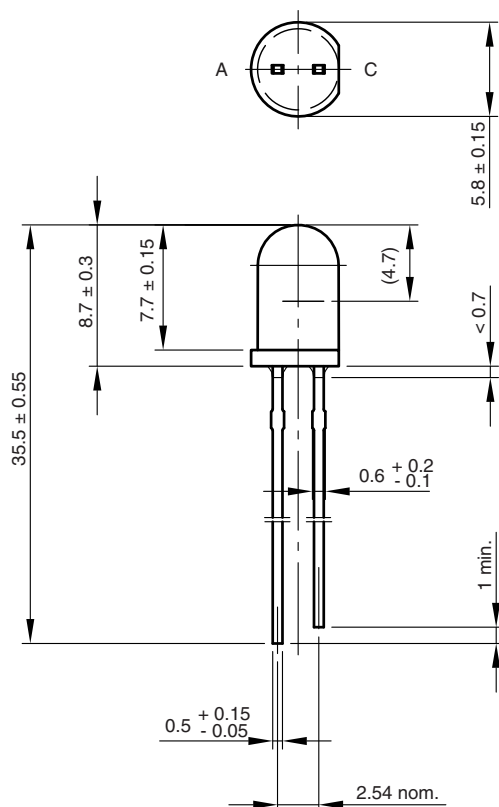


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

### PACKAGE DIMENSIONS in millimeters



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